



RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

Designed for W-CDMA and LTE base station applications with frequencies from 790 to 820 MHz. Can be used in Class AB and Class C for all typical cellular base station modulation formats.

- Typical Single-Carrier W-CDMA Performance: $V_{DD} = 28$ Volts, $I_{DQ} = 2000$ mA, $P_{out} = 96$ Watts Avg., IQ Magnitude Clipping, Channel Bandwidth = 3.84 MHz, Input Signal PAR = 7.5 dB @ 0.01% Probability on CCDF.

Frequency	G_{ps} (dB)	η_D (%)	Output PAR (dB)	ACPR (dBc)
790 MHz	20.9	35.2	6.2	-38.1
805 MHz	21.0	35.5	6.2	-38.1
820 MHz	20.9	35.7	6.1	-38.2

- Capable of Handling 10:1 VSWR, @ 32 Vdc, 805 MHz, 500 Watts CW Output Power (3 dB Input Overdrive from Rated P_{out}), Designed for Enhanced Ruggedness
- Typical P_{out} @ 1 dB Compression Point \approx 340 Watts CW

Features

- 100% PAR Tested for Guaranteed Output Power Capability
- Characterized with Series Equivalent Large-Signal Impedance Parameters and Common Source S-Parameters
- Internally Matched for Ease of Use
- Integrated ESD Protection
- Greater Negative Gate-Source Voltage Range for Improved Class C Operation
- Designed for Digital Predistortion Error Correction Systems
- Optimized for Doherty Applications
- RoHS Compliant
- In Tape and Reel. R6 Suffix = 150 Units, 56 mm Tape Width, 13 inch Reel. For R5 Tape and Reel option, see p. 14.

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +70	Vdc
Gate-Source Voltage	V_{GS}	-6.0, +10	Vdc
Operating Voltage	V_{DD}	32, +0	Vdc
Storage Temperature Range	T_{stg}	-65 to +150	$^{\circ}C$
Case Operating Temperature	T_C	150	$^{\circ}C$
Operating Junction Temperature (1,2)	T_J	225	$^{\circ}C$

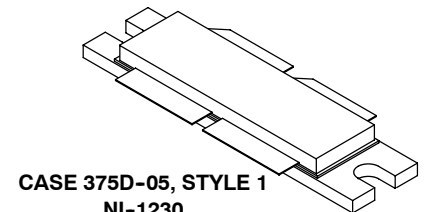
Table 2. Thermal Characteristics

Characteristic	Symbol	Value (2,3)	Unit
Thermal Resistance, Junction to Case Case Temperature 80 $^{\circ}C$, 96 W CW, 28 Vdc, $I_{DQ} = 2000$ mA, 820 MHz Case Temperature 85 $^{\circ}C$, 300 W CW, 28 Vdc, $I_{DQ} = 2000$ mA, 820 MHz	$R_{\theta JC}$	0.26 0.21	$^{\circ}C/W$

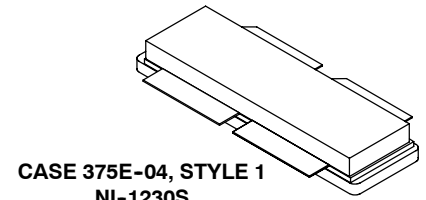
- Continuous use at maximum temperature will affect MTTF.
- MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.
- Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

MRF8P8300HR6
MRF8P8300HSR6

790-820 MHz, 96 W AVG., 28 V
SINGLE W-CDMA
LATERAL N-CHANNEL
RF POWER MOSFETs



CASE 375D-05, STYLE 1
NI-1230
MRF8P8300HR6



CASE 375E-04, STYLE 1
NI-1230S
MRF8P8300HSR6

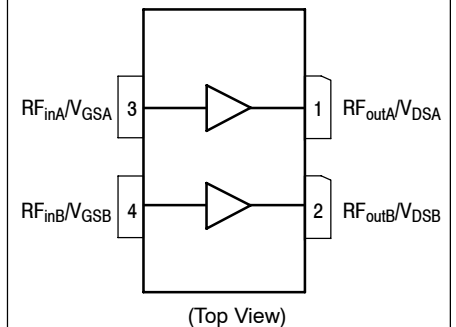


Figure 1. Pin Connections

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	2 (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

Table 4. Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics ⁽¹⁾					
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 70\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc

On Characteristics

Gate Threshold Voltage ⁽¹⁾ ($V_{DS} = 10\text{ Vdc}$, $I_D = 400\ \mu\text{Adc}$)	$V_{GS(th)}$	1.5	2.3	3.0	Vdc
Gate Quiescent Voltage ($V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 2000\text{ mA}$, Measured in Functional Test)	$V_{GS(Q)}$	2.3	3.1	3.8	Vdc
Drain-Source On-Voltage ⁽¹⁾ ($V_{GS} = 10\text{ Vdc}$, $I_D = 3\text{ Adc}$)	$V_{DS(on)}$	0.1	0.2	0.3	Vdc

Functional Tests ⁽²⁾ (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 2000\text{ mA}$, $P_{out} = 96\text{ W Avg.}$, $f = 820\text{ MHz}$, Single-Carrier W-CDMA, IQ Magnitude Clipping, Input Signal PAR = 7.5 dB @ 0.01% Probability on CCDF. ACPR measured in 3.84 MHz Channel Bandwidth @ $\pm 5\text{ MHz}$ Offset.

Power Gain	G_{ps}	20.0	20.9	23.5	dB
Drain Efficiency	η_D	34.5	35.7	—	%
Output Peak-to-Average Ratio @ 0.01% Probability on CCDF	PAR	5.9	6.1	—	dB
Adjacent Channel Power Ratio	ACPR	—	-38.2	-36.5	dBc
Input Return Loss	IRL	—	-12	-9	dB

Typical Broadband Performance (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 2000\text{ mA}$, $P_{out} = 96\text{ W Avg.}$, Single-Carrier W-CDMA, IQ Magnitude Clipping, Input Signal PAR = 7.5 dB @ 0.01% Probability on CCDF. ACPR measured in 3.84 MHz Channel Bandwidth @ $\pm 5\text{ MHz}$ Offset.

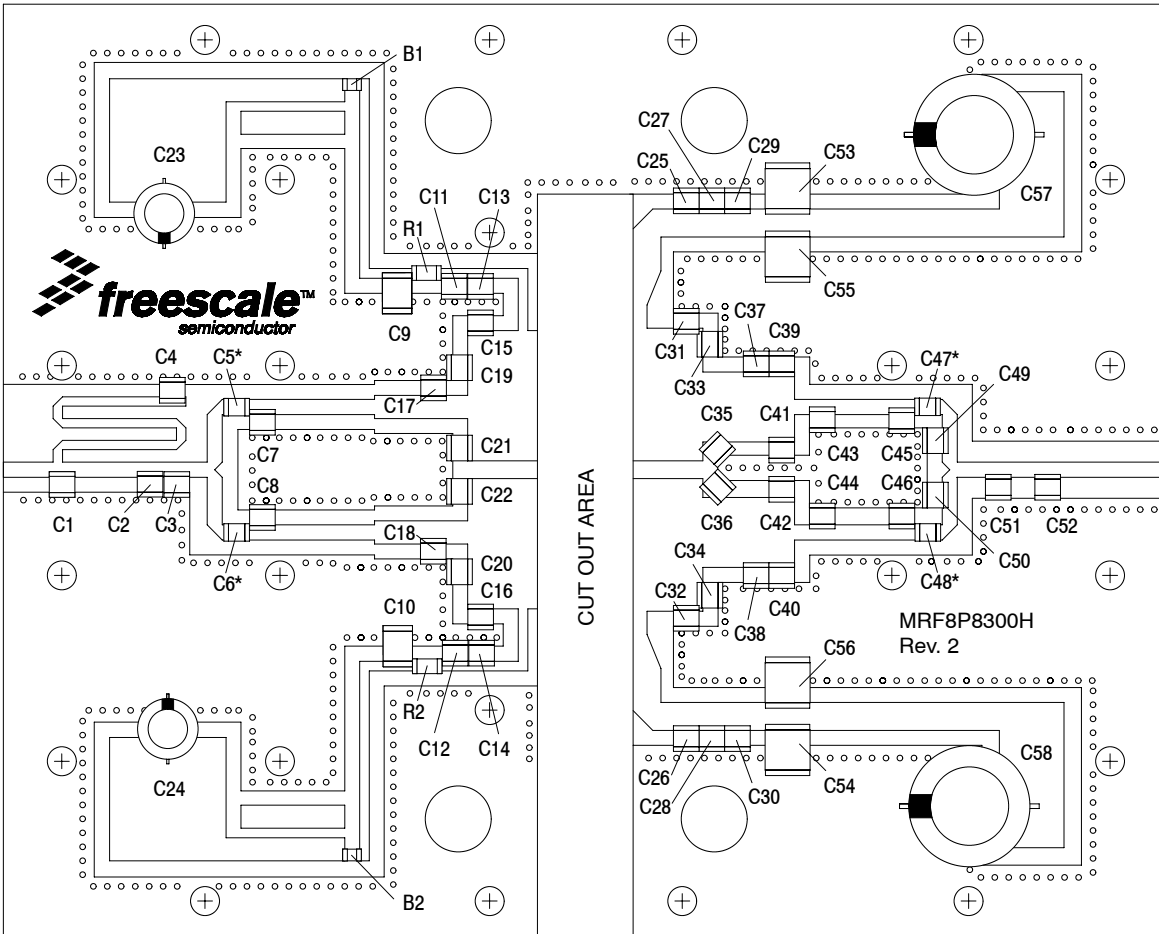
Frequency	G_{ps} (dB)	η_D (%)	Output PAR (dB)	ACPR (dBc)	IRL (dB)
790 MHz	20.9	35.2	6.2	-38.1	-11
805 MHz	21.0	35.5	6.2	-38.1	-12
820 MHz	20.9	35.7	6.1	-38.2	-12

1. Each side of device measured separately.
2. Part internally matched both on input and output.

(continued)

Table 4. Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted) (continued)

Characteristic	Symbol	Min	Typ	Max	Unit
Typical Performances (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 2000\text{ mA}$, 790–820 MHz Bandwidth					
P_{out} @ 1 dB Compression Point, CW	P1dB	—	340	—	W
IMD Symmetry @ 290 W PEP, P_{out} where IMD Third Order Intermodulation $\cong 30\text{ dBc}$ (Delta IMD Third Order Intermodulation between Upper and Lower Sidebands > 2 dB)	IMD _{sym}	—	35	—	MHz
VBW Resonance Point (IMD Third Order Intermodulation Inflection Point)	VBW _{res}	—	35	—	MHz
Gain Flatness in 30 MHz Bandwidth @ $P_{out} = 96\text{ W Avg.}$	G _F	—	0.5	—	dB
Gain Variation over Temperature (-30°C to $+85^\circ\text{C}$)	ΔG	—	0.0185	—	dB/ $^\circ\text{C}$
Output Power Variation over Temperature (-30°C to $+85^\circ\text{C}$)	$\Delta P1\text{dB}$	—	0.0076	—	dB/ $^\circ\text{C}$



*C5, C6, C47, and C48 are mounted vertically.

Figure 2. MRF8P8300HR6(HSR6) Test Circuit Component Layout

Table 5. MRF8P8300HR6(HSR6) Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
B1, B2	Short Ferrite Beads	MPZ2012S300AT000	TDK
C1, C2, C39, C40, C41, C42	2.1 pF Chip Capacitors	ATC100B2R1BT500XT	ATC
C3, C49, C50	1.0 pF Chip Capacitors	ATC100B1R0BT500XT	ATC
C4	120 pF Chip Capacitor	ATC100B121JT500XT	ATC
C5, C6, C11, C12, C47, C48	39 pF Chip Capacitors	ATC100B390JT500XT	ATC
C7, C8, C45, C46	1.1 pF Chip Capacitors	ATC100B1R1BT500XT	ATC
C9, C10	4.7 μ F, 50 V Chip Capacitors	C4532X5R1H475KT	TDK
C13, C14, C19, C20, C25, C26	10 pF Chip Capacitors	ATC100B100JT500XT	ATC
C15, C16, C35, C36	4.7 pF Chip Capacitors	ATC100B4R7CT500XT	ATC
C17, C18	4.3 pF Chip Capacitors	ATC100B4R3CT500XT	ATC
C21, C22	8.2 pF Chip Capacitors	ATC100B8R2CT500XT	ATC
C23, C24	22 μ F Electrolytic Capacitors	UUD1V220MCL1GS	Nichicon
C27, C28	20 pF Chip Capacitors	ATC100B200JT500XT	ATC
C29, C30	30 pF Chip Capacitors	ATC100B300JT500XT	ATC
C31, C32	13 pF Chip Capacitors	ATC100B130JT500XT	ATC
C33, C34	7.5 pF Chip Capacitors	ATC100B7R5CT500XT	ATC
C37, C38	1.5 pF Chip Capacitors	ATC100B1R5BT500XT	ATC
C43, C44	0.8 pF Chip Capacitors	ATC100B0R8BT500XT	ATC
C51, C52	2.0 pF Chip Capacitors	ATC100B2R0BT500XT	ATC
C53, C54, C55, C56	22 μ F, 50 V Chip Capacitors	C5750JF1H226ZT	TDK
C57, C58	470 μ F, 63 V Electrolytic Capacitors	MCGPR63V477M13X26-RH	Multicomp
R1, R2	3 Ω Chip Resistors	CRCW12063R00FNEA	Vishay
PCB	0.030", $\epsilon_r = 3.5$	RF35A2	Taconic

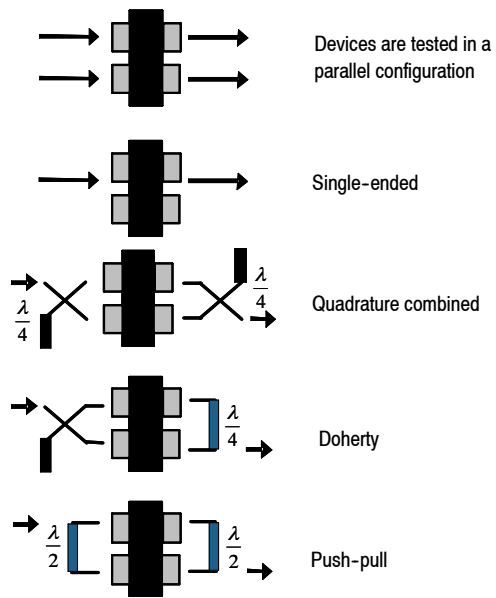


Figure 3. Possible Circuit Topologies

TYPICAL CHARACTERISTICS

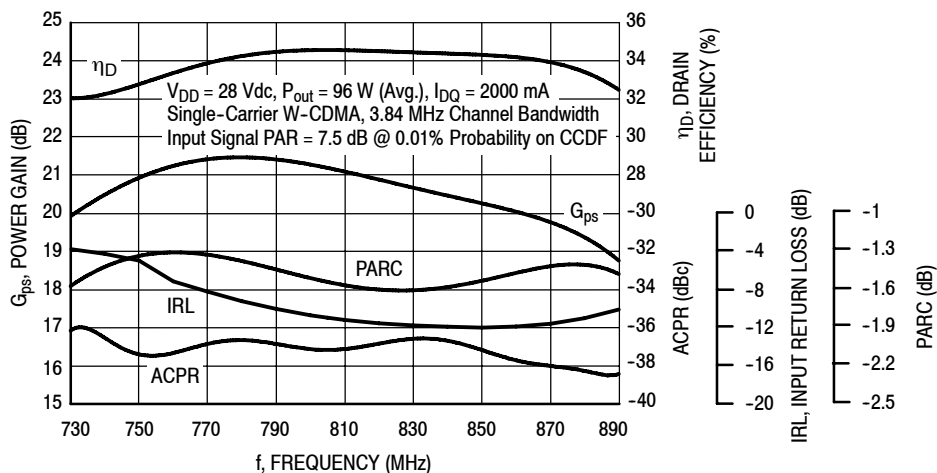


Figure 4. Output Peak-to-Average Ratio Compression (PARC) Broadband Performance @ $P_{out} = 96$ Watts Avg.

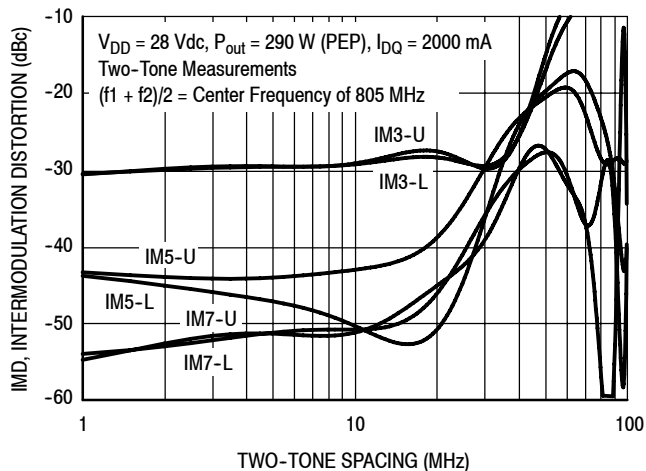


Figure 5. Intermodulation Distortion Products versus Two-Tone Spacing

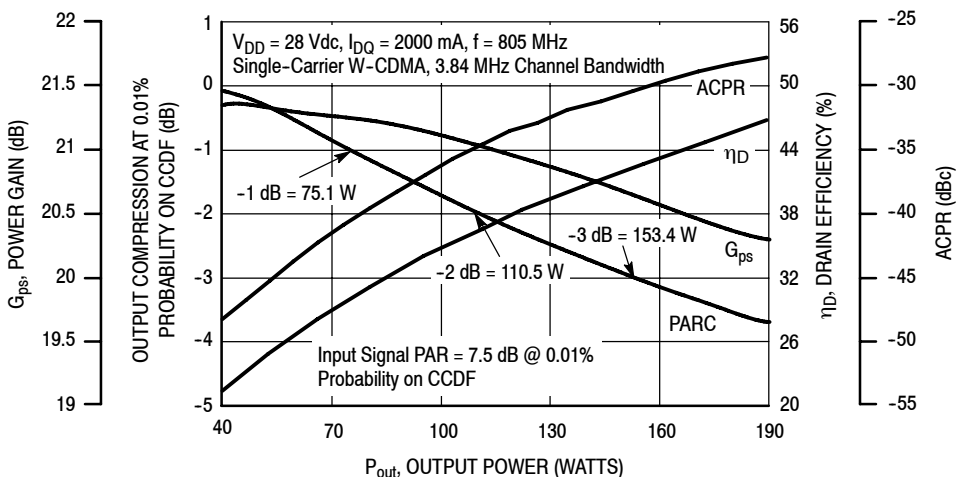


Figure 6. Output Peak-to-Average Ratio Compression (PARC) versus Output Power

TYPICAL CHARACTERISTICS

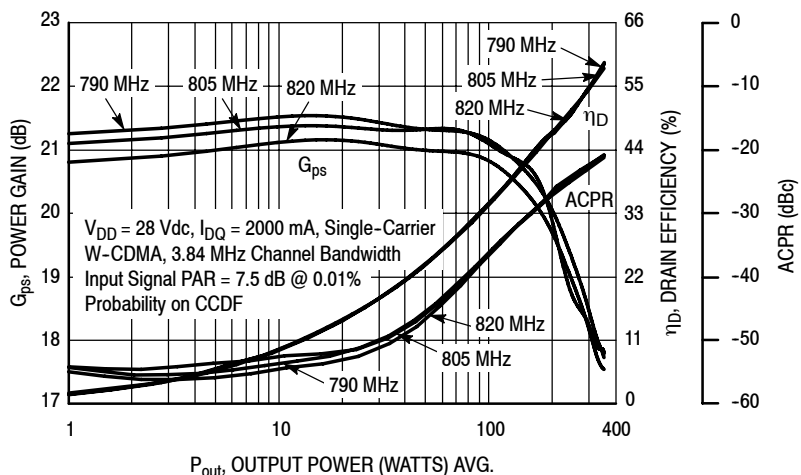


Figure 7. Single-Carrier W-CDMA Power Gain, Drain Efficiency and ACPR versus Output Power

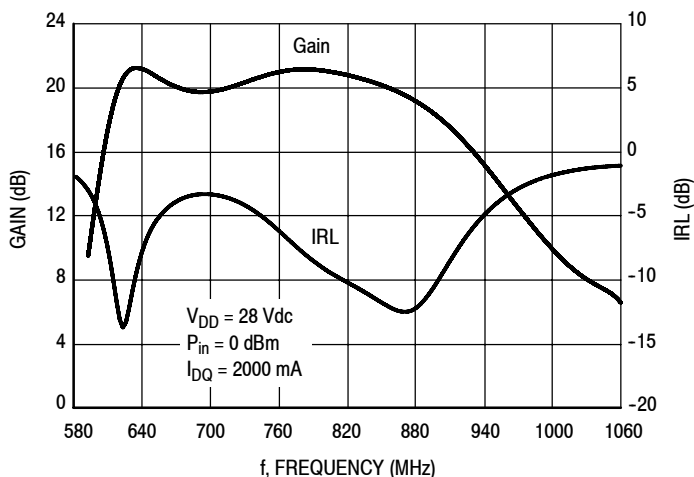


Figure 8. Broadband Frequency Response

W-CDMA TEST SIGNAL

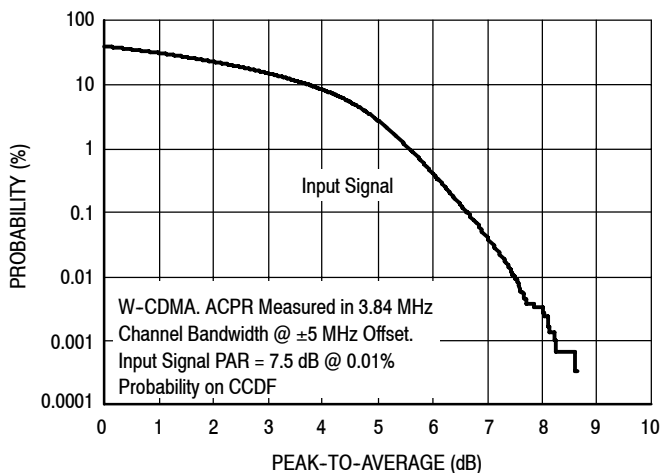


Figure 9. CCDF W-CDMA IQ Magnitude Clipping, Single-Carrier Test Signal

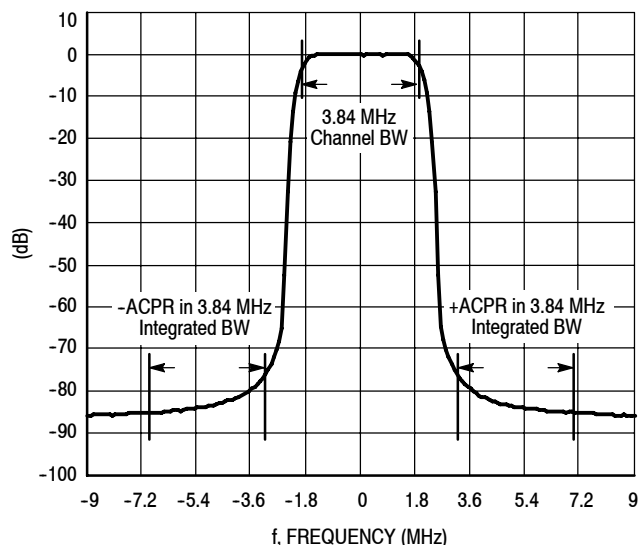


Figure 10. Single-Carrier W-CDMA Spectrum

MRF8P8300HR6 MRF8P8300HSR6

$V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 2000 \text{ mA}$, $P_{out} = 96 \text{ W Avg.}$

f MHz	Z_{source} Ω	Z_{load} Ω
730	$1.07 - j1.15$	$0.86 - j0.18$
750	$1.06 - j0.97$	$0.90 + j0.04$
770	$1.11 - j0.78$	$1.07 + j0.46$
790	$1.05 - j0.62$	$1.28 - j0.67$
810	$1.11 - j0.45$	$0.88 - j0.12$
830	$1.19 - j0.26$	$0.87 + j0.04$
850	$1.95 + j0.48$	$0.82 + j0.05$
870	$1.35 - j1.66$	$0.71 + j0.12$
890	$0.95 - j1.07$	$0.59 + j0.22$

Z_{source} = Test circuit impedance as measured from gate to ground, gate leads are tied together.

Z_{load} = Test circuit impedance as measured from drain to ground, drain leads are tied together.

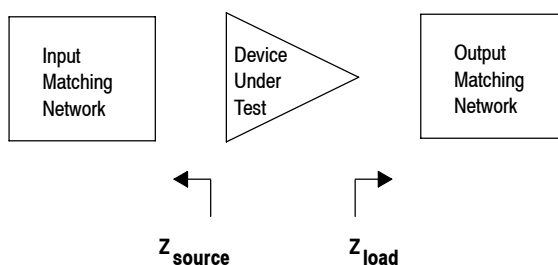
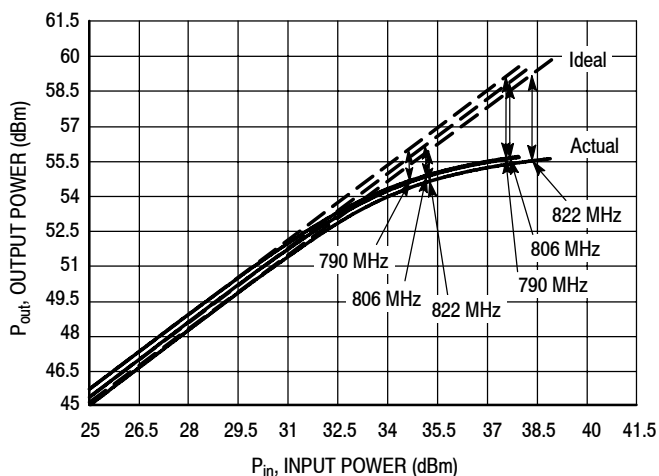


Figure 11. Series Equivalent Source and Load Impedance

ALTERNATIVE PEAK TUNE LOAD PULL CHARACTERISTICS

$V_{DD} = 28 \text{ Vdc}$, $I_{DQA} = 1000 \text{ mA}$, Pulsed CW, $10 \mu\text{sec}(\text{on})$, 10% Duty Cycle



NOTE: Load Pull Test Fixture Tuned for Peak P1dB Output Power @ 28 V

f (MHz)	P1dB		P3dB	
	Watts	dBm	Watts	dBm
790	288	54.6	363	55.6
806	299	54.8	366	55.6
822	287	54.6	349	55.4

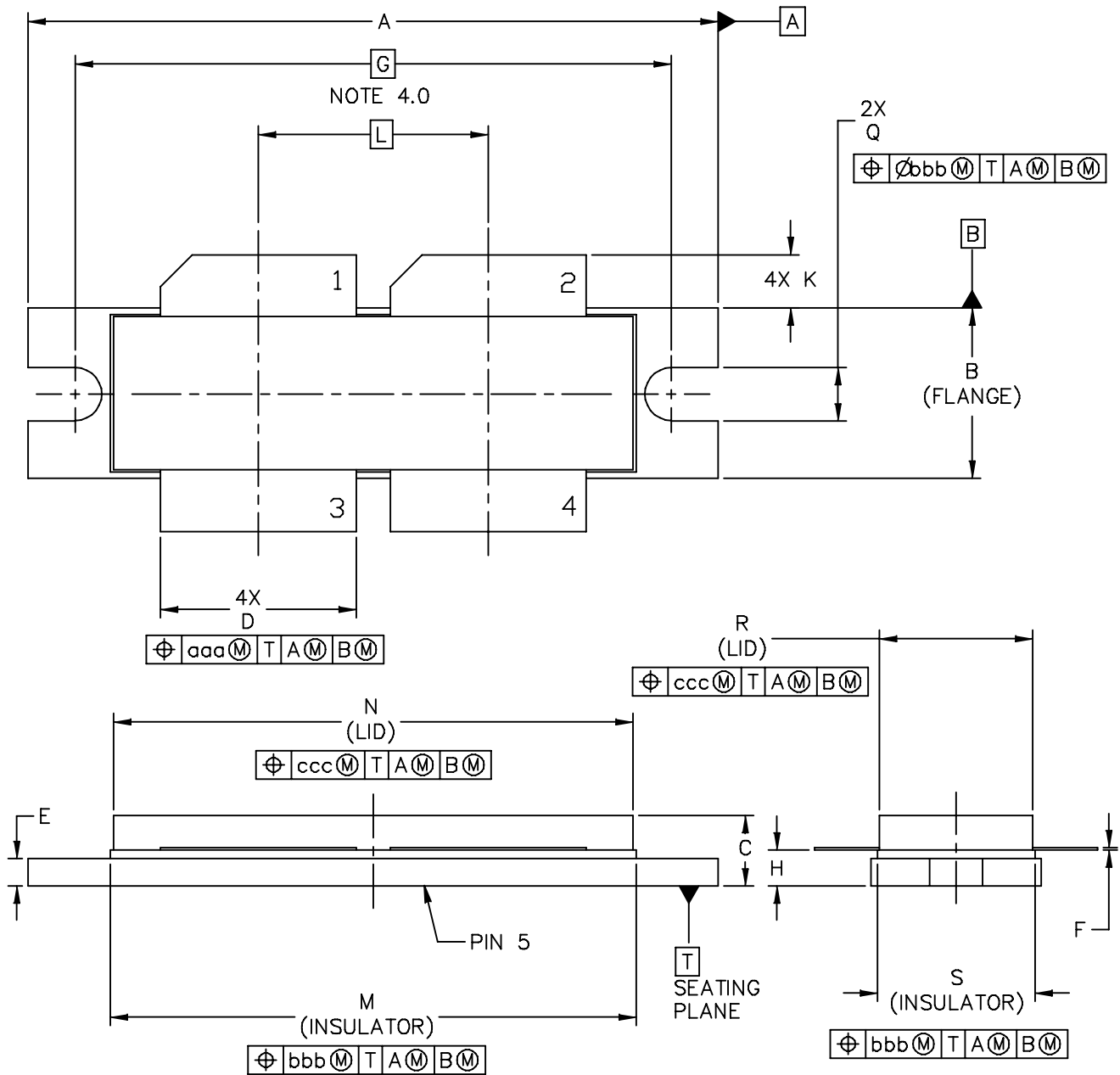
Test Impedances per Compression Level

f (MHz)		Z_{source} Ω	Z_{load} Ω
790	P1dB	$1.04 - j0.98$	$0.78 - j0.73$
806	P1dB	$1.16 - j1.39$	$0.76 - j0.71$
822	P1dB	$1.24 - j1.73$	$0.76 - j0.74$

Figure 12. Pulsed CW Output Power versus Input Power @ 28 V

NOTE: Measurement made on a per side basis.

PACKAGE DIMENSIONS



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	CASE NUMBER: 375D-05	31 MAR 2005
	STANDARD: NON-JEDEC	

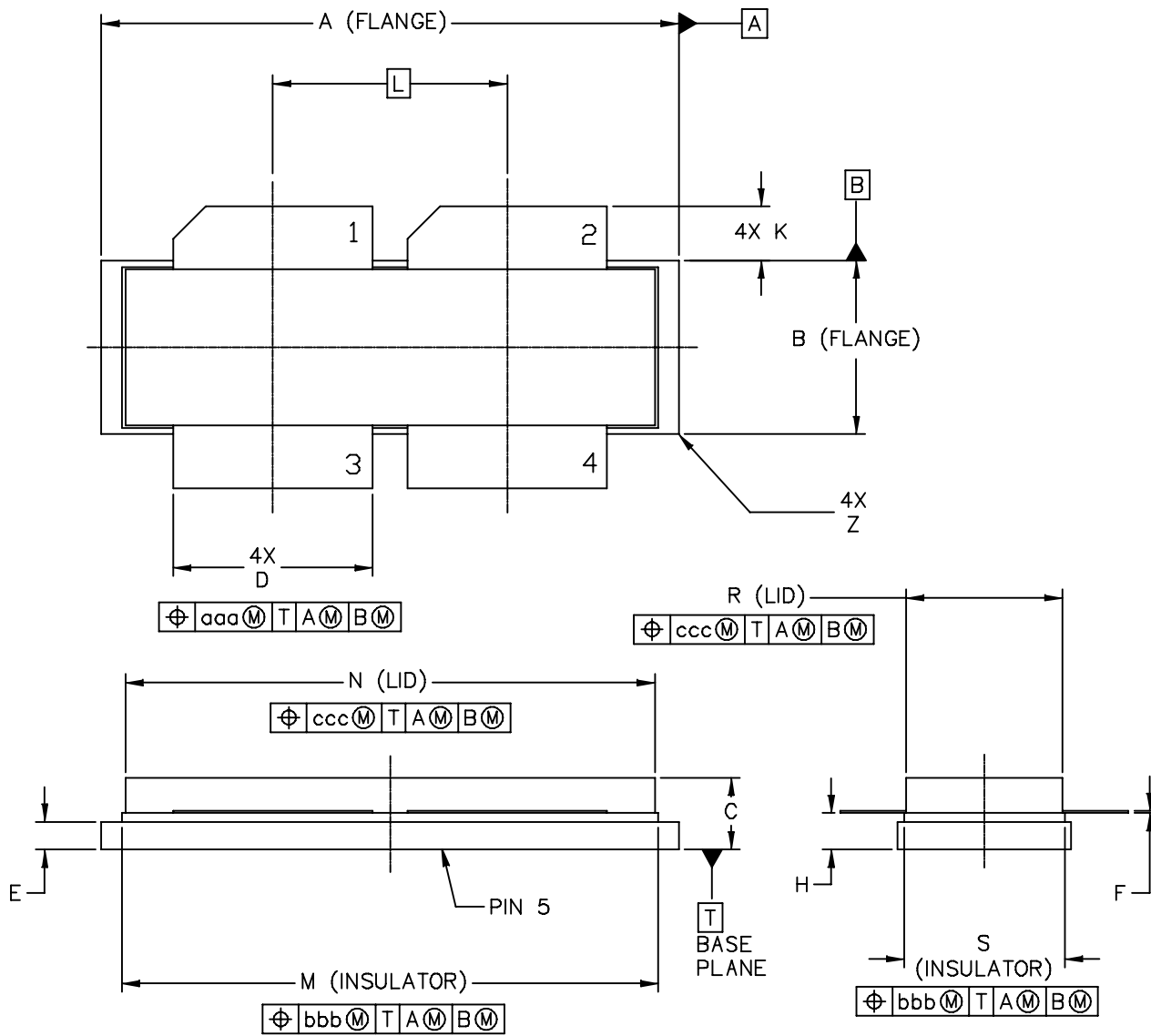
NOTES:

- 1.0 INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
- 2.0 CONTROLLING DIMENSION: INCH
- 3.0 DIMENSION H IS MEASURED .030 (0.762) AWAY FROM PACKAGE BODY.
- 4.0 RECOMMENDED BOLT CENTER DIMENSION OF 1.52 (38.61) BASED ON M3 SCREW.

STYLE 1:

- PIN 1 - DRAIN
- 2 - DRAIN
- 3 - GATE
- 4 - GATE
- 5 - SOURCE

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	1.615	1.625	41.02	41.28	N	1.218	1.242	30.94	31.55
B	.395	.405	10.03	10.29	Q	.120	.130	3.05	3.3
C	.150	.200	3.81	5.08	R	.355	.365	9.01	9.27
D	.455	.465	11.56	11.81	S	.365	.375	9.27	9.53
E	.062	.066	1.57	1.68					
F	.004	.007	0.1	0.18					
G	1.400 BSC		35.56 BSC		aaa	.013		0.33	
H	.082	.090	2.08	2.29	bbb	.010		0.25	
K	.117	.137	2.97	3.48	ccc	.020		0.51	
L	.540 BSC		13.72 BSC						
M	1.219	1.241	30.96	31.52					
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1. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH
3. DIMENSION H IS MEASURED .030 AWAY FROM PACKAGE BODY

STYLE 1:

- PIN 1 - DRAIN
- 2 - DRAIN
- 3 - GATE
- 4 - GATE
- 5 - SOURCE

DIM	INCHES		MILLIMETERS		DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	1.265	1.275	32.13	32.38	R	.355	.365	9.01	9.27
B	.395	.405	10.03	10.29	S	.365	.375	9.27	9.53
C	.150	.200	3.81	5.08	Z	---	.040	---	1.02
D	.455	.465	11.56	11.81					
E	.062	.066	1.57	1.68	aaa	.013		0.33	
F	.004	.007	0.1	0.18	bbb	.010		0.25	
H	.082	.090	2.08	2.29	ccc	.020		0.51	
K	.117	.137	2.97	3.48					
L	.540 BSC		13.72 BSC						
M	1.219	1.241	30.96	31.52					
N	1.218	1.242	30.94	31.55					
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PRODUCT DOCUMENTATION, TOOLS AND SOFTWARE

Refer to the following documents, tools and software to aid your design process.

Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

Software

- Electromigration MTTF Calculator
- RF High Power Model
- .s2p File

For Software and Tools, do a Part Number search at <http://www.freescale.com>, and select the "Part Number" link. Go to the Software & Tools tab on the part's Product Summary page to download the respective tool.

R5 TAPE AND REEL OPTION

R5 Suffix = 50 Units, 56 mm Tape Width, 13 inch Reel.

The R5 tape and reel option for MRF8P8300H and MRF8P8300HS parts will be available for 2 years after release of MRF8P8300H and MRF8P8300HS. Freescale Semiconductor, Inc. reserves the right to limit the quantities that will be delivered in the R5 tape and reel option. At the end of the 2 year period customers who have purchased these devices in the R5 tape and reel option will be offered MRF8P8300H and MRF8P8300HS in the R6 tape and reel option.

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	Jan. 2011	• Initial Release of Data Sheet

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